



2/25/04

<b>INFORMATION DISCLOSURE CITATION</b> (Use several sheets if necessary)		Docket Number (Optional)	Application Number
		OKI.227	09/825,973 <del>NEW</del>
		Applicant(s) Norio HIRASHITA et al.	
		Filing Date	Group Art Unit
		APRIL 5, 2001	2823 <del>TO BE ASSIGNED</del>
*EXAMINER INITIAL	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
JM	A	Deep sub-0.1 um MOSFET's with Very Thin SOL Layer for Ultra-Low Power Applicants, Information and Communication Engineers C-II Vol. J81-C-II No. 3, pp. 313-319, August 1998.	
JM	B	Optimization of Series Resistance in Sub-0.2 um SOI MOSFET's, IEEE Electron Device letters, VOL. 15, No. 9, September 1994, p. 363-365.	
JM	C	Optimization of series resistance in Sub-0.2 um SOI MOSFET's, 1993 IEEE, pp. IEDM93-723-726-IEDM 93.	
EXAMINER		DATE CONSIDERED	
/Julio Maldonado/ (11/25/2006)		11/25/2006	
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

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